

ABSTRACT OF THE DISCLOSURE

A method for forming a self-aligned contact hole includes forming a plurality of conductive structures on a semiconductor substrate, each conductive structure including a conductive film pattern and a protection pattern formed on the conductive film pattern, forming a first insulation film to fill a space between adjacent conductive structures, successively etching the first insulation film and the protection patterns until each of the protection patterns has an exposed level upper surface, forming a second insulation film on the resultant structure, and selectively etching portions of the second insulation film and the first insulation film using a photolithography process to form the self-aligned contact hole exposing a portion of the semiconductor substrate between adjacent conductive structures. Process failures generated during formation of a self-aligned contact hole can thus be prevented because a nitride pattern capping a conductive film pattern remains, thereby enhancing reliability and yield of a semiconductor device.